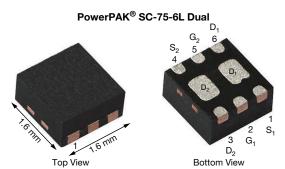




Dual N-Channel 20 V MOSFET



Marking code: CA

PRODUCT SUMMARY									
V _{DS} (V)	20								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.216								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 2.5 \text{ V}$	0.268								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 1.8 \text{ V}$	0.375								
Q _g typ. (nC)	1.2								
I _D (A) ^{a, g}	1.5								
Configuration	Dual								

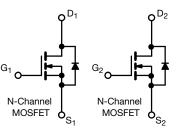
FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-75 package
 - Small footprint area
 - Low on-resistance
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT HALOGEN FREE

APPLICATIONS

- · Load switch, PA switch, and battery switch for portable devices
- DC/DC converter



ORDERING INFORMATION						
Package	PowerPAK SC-75					
Lead (Pb)-free and halogen-free	SiB912DK-T1-GE3					

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)								
PARAMETER		SYMBOL	LIMIT	UNIT				
Drain-source voltage		V_{DS}	20	V				
Gate-source voltage		V_{GS}	S ±8					
	T _C = 25 °C		1.5 ^a					
Continuous drain surrent (T = 150 °C)	T _C = 70 °C		1.5 ^a					
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	I _D	1.5 ^{a, b, c}					
	T _A = 70 °C		1.4 ^{b, c}	Α				
Pulsed drain current		I _{DM}	5					
O all a constant and all all all a constant	T _C = 25 °C	1	1.5 ^a					
Continuous source-drain diode current	T _A = 25 °C	I _S	0.9 b, c					
	T _C = 25 °C		3.1					
Maximum navvar dissination	T _C = 70 °C		2	w				
Maximum power dissipation	T _A = 25 °C	P _D	1.1 ^{b, c}	VV				
	T _A = 70 °C		0.7 b, c					
Operating junction and storage temperature ran	ge	T _J , T _{stg}	-55 to +150	°C				
Soldering recommendations (peak temperature)	d, e	, and the second	260	C				

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	90	115	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	32	40	C/VV				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- 6. See solder profile (<u>www.vishav.com/doc?73257</u>). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components Maximum under steady state conditions is 125 °C/W
- g. Based on $T_C = 25\ ^{\circ}C$



www.vishay.com

Vishay Siliconix

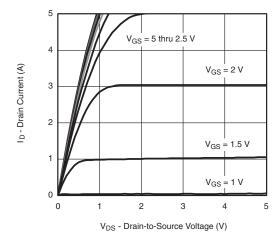
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	<u>.</u>			•		ı
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	L 050 A	-	22	-	
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-2	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.4	-	1	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	-	-	±100	nA
Zana mata walta na alusin awamat	,	V _{DS} = 20 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	μΑ
On-state drain current a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	5	-	-	Α
	, ,	V _{GS} = 4.5 V, I _D = 1.8 A	-	0.180	0.216	Ω
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 1.6 \text{ A}$	-	0.223	0.268	
		$V_{GS} = 1.8 \text{ V}, I_D = 0.3 \text{ A}$	-	0.300	0.375	
Forward transconductance a	9 _{fs}	V _{DS} = 10 V, I _D = 1.8 A	-	3	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	95	-	
Output capacitance	Coss	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	24	-	pF
Reverse transfer capacitance	C _{rss}		-	11	-	
-		$V_{DS} = 10 \text{ V}, V_{GS} = 8 \text{ V}, I_{D} = 1.8 \text{ A}$	-	2	3	nC
Total gate charge	Q _g		-	1.2	1.8	
Gate-source charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 1.8 \text{ A}$	-	0.3	-	
Gate-drain charge	Q _{qd}		-	0.15	-	
Gate resistance	R_g	f = 1 MHz	0.5	2.5	5	Ω
Turn-on delay time	t _{d(on)}		-	5	10	
Rise time	t _r	$V_{DD} = 10 \text{ V}, R_L = 7.1 \Omega,$	-	10	20	- - - ns
Turn-off delay time	t _{d(off)}	$I_D \cong 1.4 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	24	36	
Fall time	t _f		-	8	16	
Turn-on delay time	t _{d(on)}		-	2	4	
Rise time	t _r	$V_{DD} = 10 \text{ V}, R_L = 7.1 \Omega,$	-	9	18	
Turn-off delay time			-	8	16	1
Fall time	t _f		-	7	14	
Drain-Source Body Diode Characterist	ics					
Continuous source-drain diode current c	I _S	T _C = 25 °C	-	-	1.5	
Pulse diode forward current	I _{SM}		-	-	5	Α
Body diode voltage	V _{SD}	I _S = 1.4 A, V _{GS} = 0 V	-	0.7	1.2	٧
Body diode reverse recovery time	t _{rr}	- 40	-	9	18	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = 1.4 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	3	6	nC
Reverse recovery fall time	t _a	$T_{J} = 25 ^{\circ}\text{C}$	-	6	-	
Reverse recovery rise time	t _b	-	_	3		ns

Notes

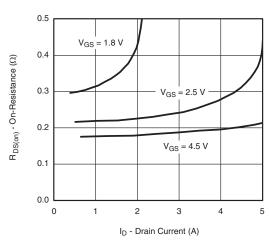
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Package limited

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

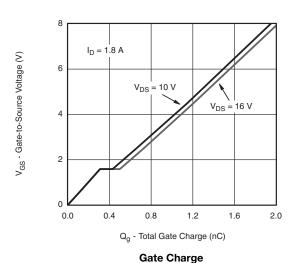


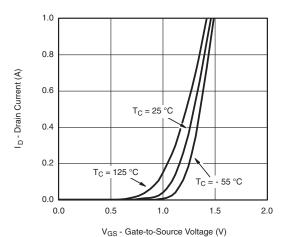


Output Characteristics

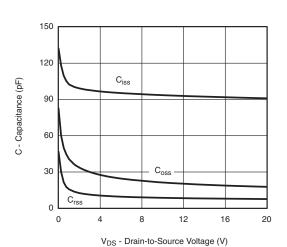


On-Resistance vs. Drain Current and Gate Voltage

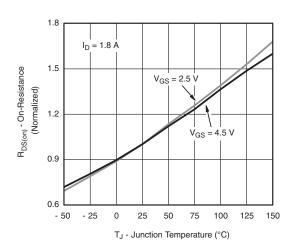




Transfer Characteristics

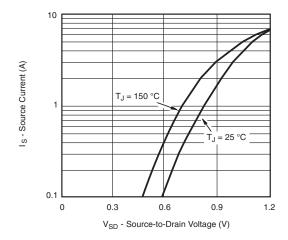


Capacitance

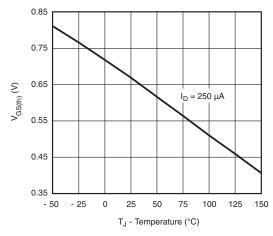


On-Resistance vs. Junction Temperature

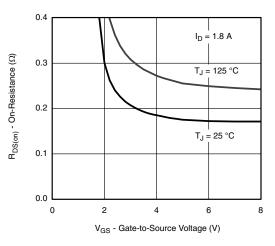




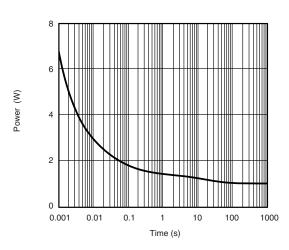
Source-Drain Diode Forward Voltage



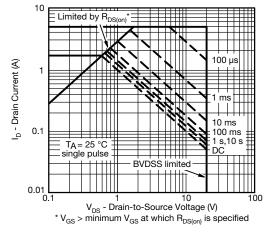
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

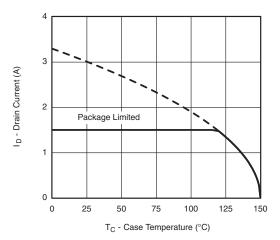


Single Pulse Power, Junction-to-Ambient

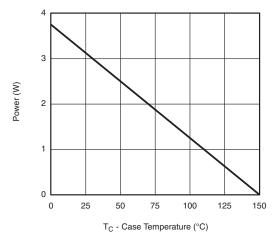


Safe Operating Area, Junction-to-Case

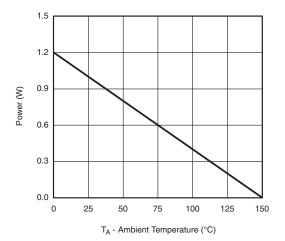




Current Derating a



Power Derating, Junction-to-Case

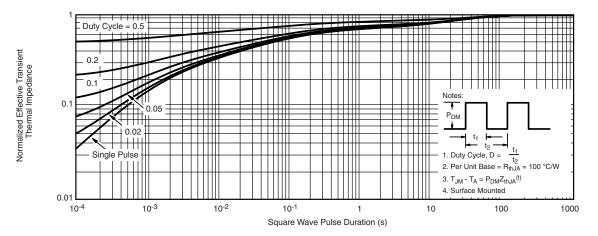


Power Derating, Junction-to-Ambient

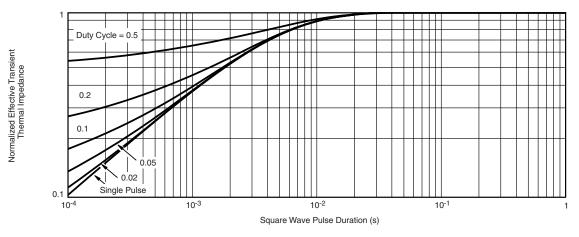
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



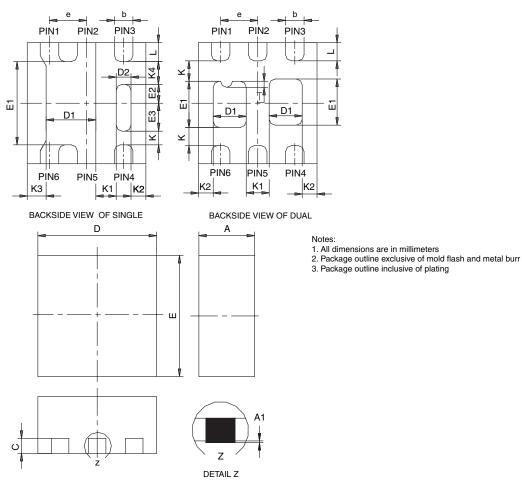
Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK® SC75-6L



	SINGLE PAD						DUAL PAD						
DIM	M	ILLIMETE	RS	INCHES MILLIMETERS		RS		INCHES					
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021	
D2	0.10	0.20	0.30	0.004	0.008	0.012							
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028	
E2	0.20	0.25	0.30	0.008	0.010	0.012							
E3	0.32	0.37	0.42	0.013	0.015	0.017							
е		0.50 BSC			0.020 BSC	;	0.50 BSC			0.020 BSC			
K		0.180 TYP)		0.007 TYP			0.245 TYP			0.010 TYP		
K1		0.275 TYP	١	0.011 TYP			0.320 TYP			0.013 TYP			
K2		0.200 TYP	P 0.008 TYP			0.200 BSC			0.008 TYP				
К3		0.255 TYP 0.010 TYP				•							
K4		0.300 TYP 0.012 TYP											
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014	
T							0.03	0.08	0.13	0.001	0.003	0.005	

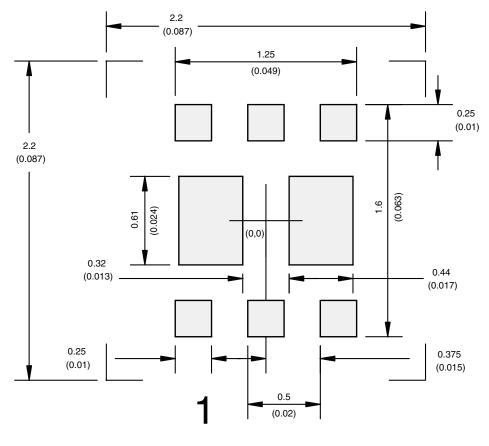
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RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Dual



Dimensions in mm/(Inches)

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APPLICATION NOTE



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